

# Mingda Zhu

## List of Publications by Year in descending order

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26  
papers

1,325  
citations

623734

14  
h-index

839539

18  
g-index

26  
all docs

26  
docs citations

26  
times ranked

1790  
citing authors

#	ARTICLE	IF	CITATIONS
1	Extraordinary Control of Terahertz Beam Reflectance in Graphene Electro-absorption Modulators. Nano Letters, 2012, 12, 4518-4522.	9.1	235
2	1.9-kV AlGaIn/GaN Lateral Schottky Barrier Diodes on Silicon. IEEE Electron Device Letters, 2015, 36, 375-377.	3.9	160
3	1.7-kV and 0.55- $\text{ext}\{m\}\Omega \cdot \text{ext}\{cm\}^{\wedge}\{2\}$ GaN p-n Diodes on Bulk GaN Substrates With Avalanche Capability. IEEE Electron Device Letters, 2016, 37, 161-164.	3.9	153
4	Near unity ideality factor and Shockley-Read-Hall lifetime in GaN-on-GaN <i>p-n</i> diodes with avalanche breakdown. Applied Physics Letters, 2015, 107, .	3.3	146
5	Terahertz imaging employing graphene modulator arrays. Optics Express, 2013, 21, 2324.	3.4	113
6	Efficient terahertz electro-absorption modulation employing graphene plasmonic structures. Applied Physics Letters, 2012, 101, .	3.3	103
7	1.1-kV Vertical GaN p-n Diodes With p-GaN Regrown by Molecular Beam Epitaxy. IEEE Electron Device Letters, 2017, 38, 1071-1074.	3.9	60
8	High breakdown single-crystal GaN p-n diodes by molecular beam epitaxy. Applied Physics Letters, 2015, 107, .	3.3	53
9	Strained GaN quantum-well FETs on single crystal bulk AlN substrates. Applied Physics Letters, 2017, 110, .	3.3	48
10	Development of GaN Vertical Trench-MOSFET With MBE Regrown Channel. IEEE Transactions on Electron Devices, 2018, 65, 2558-2564.	3.0	46
11	Two-dimensional electron gases in strained quantum wells for AlN/GaN/AlN double heterostructure field-effect transistors on AlN. Applied Physics Letters, 2014, 104, .	3.3	42
12	Ultralow-Leakage AlGaIn/GaN High Electron Mobility Transistors on Si With Non-Alloyed Regrown Ohmic Contacts. IEEE Electron Device Letters, 2016, 37, 16-19.	3.9	37
13	Activation of buried p-GaN in MOCVD-regrown vertical structures. Applied Physics Letters, 2018, 113, 062105.	3.3	35
14	Realization of GaN PolarMOS using selective-area regrowth by MBE and its breakdown mechanisms. Japanese Journal of Applied Physics, 2019, 58, SCCD15.	1.5	18
15	600 V GaN vertical V-trench MOSFET with MBE regrown channel. , 2017, , .		14
16	Dual optical marker Raman characterization of strained GaN-channels on AlN using AlN/GaN/AlN quantum wells and $^{15}\text{N}$ isotopes. Applied Physics Letters, 2015, 106, .	3.3	13
17	Electron mobility in polarization-doped Al <sub>0.2</sub> GaN with a low concentration near $10^{17} \text{ cm}^{-3}$ . Applied Physics Letters, 2017, 110, 182102.	3.3	11
18	AlGaIn/GaN HEMTs on Si by MBE with regrown contacts and $f_{\text{T}} = 153 \text{ GHz}$ . Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 887-889.	0.8	10

#	ARTICLE	IF	CITATIONS
19	GaN vertical nanowire and fin power MISFETs. , 2017, , .		8
20	Unique opportunity to harness polarization in GaN to override the conventional power electronics figure-of-merits. , 2015, , .		7
21	High-voltage polarization-induced vertical heterostructure p-n junction diodes on bulk GaN substrates. , 2015, , .		3
22	Distributed polarization-doped GaN p-n diodes with near-unity ideality factor and avalanche breakdown voltage of 1.25 kV. Applied Physics Letters, 2022, 120, .	3.3	3
23	GaN lateral PolarSJs: Polarization-doped super junctions. , 2014, , .		2
24	Comparing buffer leakage in PolarMOSH on SiC and free-standing GaN substrates. , 2016, , .		2
25	Enhancement of punch-through voltage in GaN with buried p-type layer utilizing polarization-induced doping. , 2018, , .		2
26	Vertical Ga <sub>0.2</sub> O <sub>0.3</sub> Schottky barrier diodes on single-crystal $\sqrt{2}$ -Ga <sub>0.2</sub> O <sub>0.3</sub> ( $\sqrt{2}$ 201) substrates. , 2016, , .		1